In response to the Official Action dated May 14, 1996, please amend the above-identified application as follows:

In the Claims:

Please amend claims 8, 21, 27, 41, 42, 44-46 as follows:

8. (Twice Amended) An apparatus for processing a semiconductor on a substrate comprising:

an irradiation apparatus for irradiating a [linear] laser light having a rectangular form to said semiconductor therein;

a vacuum apparatus for a vacuum processing; and

a mechanism for transporting said substrate from said vacuum apparatus to said irradiation apparatus without exposing said substrate to outside air,

wherein said semiconductor on said substrate is moved during the irradiation of said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said semiconductor, to scan said semiconductor with said laser light over a whole surface of said substrate.

21. (Twice Amended) An apparatus for processing a semiconductor device comprising at least a light processing chamber for treating a substrate with a [linear] laser light having a rectangular form therein by irradiating said substrate with said [linear] laser light through a light window provided on a wall of said light processing chamber and an evacuable chamber for performing a vacuum treatment therein, wherein said apparatus is provided with a means for transferring an object from said light processing chamber to

said evacuable chamber, or vice versa without exposing said object to air, and wherein said substrate is moved in a direction perpendicularly to said [linear] laser light in said light processing chamber during the irradiation of said substrate with said [linear] laser light to crystallize an entire semiconductor film provided on said substrate.

27. (Twice Amended) An apparatus for processing a semiconductor device comprising:

a first chamber for treating an object provided on a substrate with a [linear] laser light having a rectangular form therein;

a second chamber for treating said object; and

a transferring means for transferring said object from said first chamber to said second chamber without exposing said object to air,

wherein said object provided on said substrate is moved during the treatment of said object with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said object, to scan said object with said laser light over a whole surface of said substrate.

41. (Amended) An apparatus for fabricating a semiconductor device comprising:

a first chamber for conducting ion doping on a substrate therein; and

a second chamber for treating said substrate with a [linear] laser light having a rectangular form therein after said ion doping,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air, and

wherein said substrate is moved during the treatment of said substrate with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said substrate, to scan a whole surface of said substrate with said laser light.

42. (Amended) An apparatus for fabricating a semiconductor device comprising:

a first chamber for conducting plasma doping on a substrate therein; and

a second chamber for annealing said substrate with a [linear] laser light having a rectangular form therein after said plasma doping,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air, and

wherein said substrate is moved during the annealing of said substrate with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said substrate, to scan a whole surface of said substrate with said laser light.

44. (Amended) An apparatus for fabricating a semiconductor device comprising:

a first chamber for conducting plasma chemical vapor deposition on a substrate therein; and

a second chamber for annealing said substrate with a [linear] laser light having a rectangular form therein after said plasma chemical vapor deposition,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air, and

wherein said substrate is moved during the annealing of said substrate with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said substrate, to scan a whole surface of said substrate with said laser light.

45. (Amended) An apparatus for fabricating a semiconductor device comprising:

a first chamber for treating a substrate with a [linear] laser light having a rectangular form therein; and

a second chamber for heating said substrate in hydrogen atmosphere therein after said treating,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air, and

wherein said substrate is moved during the treatment of said substrate with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said substrate, to scan a whole surface of said substrate with said laser light.

46. (Amended) An apparatus for fabricating a semiconductor device comprising:

a first chamber for loading and unloading a substrate; and

a second chamber for scanning said substrate with a [linear] laser light having a rectangular form therein to conduct crystallization or activation on said substrate,

wherein said apparatus is provided with a means for transferring said substrate from said first chamber to said second chamber without exposing said substrate to air,

wherein said substrate is moved during the scanning of said substrate with said laser light so that a length of said laser light is longer than a length of said substrate on a surface of said substrate, to scan a whole surface of said substrate with said laser light.

Please add claims 47-54 as follows:

--47. The apparatus of claim 8 wherein said substrate has a size of 300 mm by 400 mm, and said laser light having a rectangular form has a size of 2 mm x 350 mm.

48. The apparatus of claim 21 wherein said substrate has a size of 300 mm by 400 mm, and said laser light having a rectangular form has a size of 2 mm x 350 mm.

49. The apparatus of claim 27 wherein said substrate has a size of 300 mm by 400 mm, and said laser light having a rectangular form has a size of 2 mm x 350 mm.